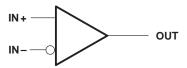
- Wide Range of Supply Voltages 2 V to 8 V
- Fully Characterized at 3 V and 5 V
- Very-Low Supply-Current Drain
 120 μA Typ at 3 V
- Output Compatible With TTL, MOS, and CMOS
- Fast Response Time . . . 200 ns Typ for TTL-Level Input Step

- High Input Impedance . . . 10¹² Ω Typ
- Extremely Low Input Bias Current 5 pA Typ
- Common-Mode Input Voltage Range Includes Ground
- Built-In ESD Protection

description

The TLV2352 consists of two independent, low-power comparators specifically designed for single power-supply applications and operates with power-supply rails as low as 2 V. When powered from a 3-V supply, the typical supply current is only 120 μ A.

symbol (each comparator)



The TLV2352 is designed using the Texas Instruments LinCMOSTM technology and therefore features an extremely high input impedance (typically greater than $10^{12}\,\Omega$), which allows direct interfacing with high-impedance sources. The outputs are N-channel open-drain configurations that require an external pullup resistor to provide a positive output voltage swing, and they can be connected to achieve positive-logic wired-AND relationships. The TLV2352I is fully characterized at 3 V and 5 V for operation from – 40°C to 85°C. The TLV2352M is fully characterized at 3 V and 5 V for operation from – 55°C to 125°C.

The TLV2352 has internal electrostatic-discharge (ESD)-protection circuits and has been classified with a 1000-V ESD rating using Human Body Model testing. However, care should be exercised in handling this device as exposure to ESD may result in degradation of the device parametric performance.

AVAILABLE OPTIONS

				PACKAGE	DEVICES			CHIP	
TA	V _{IO} max at 25°C	SMALL OUTLINE (D) [†]	CHIP CARRIER (FK)	ARRIER DIP		PLASTIC TSSOP (P) (PW)‡		FORM (Y)	
-40°C to 85°C	5 mV	TLV2352ID		_	TLV2352IP	TLV2352IPWLE		TLV2352Y	
−55°C to 125°C	5 mV	_	TLV2352MFK	TLV2352MJG	_	_	TLV2352MU	1LV23321	

[†] The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLV2352IDR).



These devices have limited built-in protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

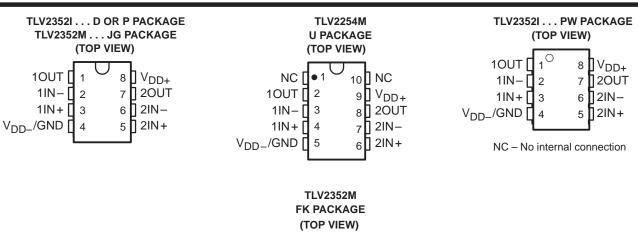
LinCMOS is a trademark of Texas Instruments Incorporated.



[‡]The PW packages are only available left-ended taped and reeled (e.g., TLV2352IPWLE)

TLV2352, TLV2352Y LinCMOS™ DUAL LOW-VOLTAGE DIFFERENTIAL COMPARATORS

SLCS011B - MAY 1992 - REVISED MARCH 1999



NC VDD+

3 2 1 20 19

9 10 11 12 13

NC

17 ∏

16 NC

15

2OUT

2IN-

NC

NC

5

NC 6

7

П 8

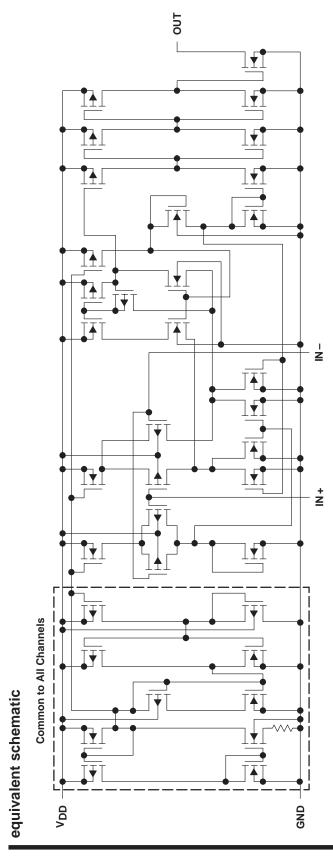
1IN-

1IN+

NC

INSTRUMENTS

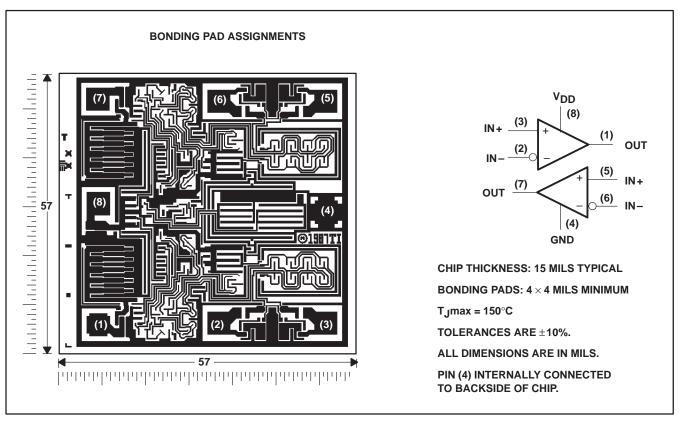
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265





TLV2352Y chip information

These chips, when properly assembled, display characteristics similar to the TLV2352. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. This chip can be mounted with conductive epoxy or a gold-silicon preform.



TLV2352, TLV2352Y LinCMOS™ DUAL LOW-VOLTAGE DIFFERENTIAL COMPARATORS

SLCS011B - MAY 1992 - REVISED MARCH 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	8 V
Differential input voltage, V _{ID} (see Note 2)	
Input voltage range, V _I	0.3 to 8 V
Output voltage, VO	8 V
Input current, I ₁	
Output current, I _O	20 mA
Duration of output short-circuit current to GND (see Note 3)	unlimited
Continuous total power dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A : TLV2352I	40°C to 85°C
TLV2352M	–55°C to 125°C
Storage temperature range, T _{stq}	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, P, and PV	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: FK, JG, and	U Packages 300°C

[†] Stress beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. Short circuits from outputs to $V_{\mbox{DD}}$ can cause excessive heating and eventual device destruction.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	377 mW	_
FK	1375 mW	11.0 mW/°C	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	546 mW	210 mW
Р	1000 mW	8.0 mW/°C	520 mW	_
PW	525 mW	4.2 mW/°C	273 mW	_
U	700 mW	5.5 mW/°C	370 mW	150 mW

recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V _{DD}		2	8	V
Common mode input voltage V	V _{DD} = 3 V	0	1.75	V
Common-mode input voltage, V _{IC}	V _{DD} = 5 V	0	3.75	V
Operating free-air temperature, T _A	TLV2352I	-40	85	°C
Operating free-air temperature, 14	TLV2352M	-55	125)

electrical characteristics at specified free-air temperature

							TLV2	.352I			
	PARAMETER	TEST CON	IDITIONS	T _A ‡	V	_{DD} = 3 V	'	VI	_{DD} = 5 V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V. 0	Input offeet voltage	\/.a - \/.a=min	Soo Note 4	25°C		1	5		1	5	mV
VIO	Input offset voltage	$V_{IC} = V_{ICRmin}$	See Note 4	Full range			7			7	IIIV
lio.	Input offset current			25°C		1			1		pА
110	input onset current			85°C			1			1	nA
lin.	Input bias current			25°C		5			5		pA
ΙΒ	input bias current			85°C			2			2	nA
	Common-mode input			25°C	0 to 2			0 to 4			
VICR	voltage range			Full range	0 to 1.75			0 to 3.75			V
1	High-level output	V:= - 1 V		25°C		0.1			0.1		nA
ЮН	current	V _{ID} = 1 V		Full range			1			1	μΑ
VOL	Low-level output	V _{ID} = −1 V,	I _{OL} = 2 mA	25°C		115	300		150	400	mV
VOL	voltage	ν ₁ D = - τ ν,	IOL = 2 IIIA	Full range			600			700	IIIV
l _{OL}	Low-level output current	V _{ID} = -1 V,	V _{OL} = 1.5 V	25°C	6	16		6	16		mA
IDD	Supply current	V _{ID} = 1 V,	No load	25°C		120	250		140	300	
IDD	очрріу сипепі	ν _{ID} = τ ν,	INO IOAU	Full range			350			400	μΑ

[†] All characteristics are measured with zero common-mode input voltages unless otherwise noted.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with VDD = 5 V, 2 V with VDD = 3 V, or below 400 mV with a 10-k Ω resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, $V_{DD} = 3 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER			DITIONS	Т	UNIT		
PARAMETER			MIN	TYP	MAX	UNIT	
Response time	$R_L = 5.1 \text{ k}\Omega$,	C _L = 15 pF§,	100-mV input step with 5-mV overdrive		640		ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses VO = 1 V with $V_{DD} = 3 \text{ V or } V_O = 1.4 \text{ V with } V_{DD} = 5 \text{ V}.$

switching characteristics, V_{DD} = 5 V, T_A = 25°C

PARAMETER			DITIONS	Т	UNIT			
PARAMETER			TEST CON	BITIONS	MIN	TYP	MAX	UNIT
Response time	D 5.1 kO	C 15 pE8	Con Noto F	100-mV input step with 5-mV overdrive		650		no
Response time	$R_L = 5.1 \text{ k}\Omega$, $C_L = 15 \text{ pF}$, See Note			TTL-level input step	200			ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses VO = 1 V with $V_{DD} = 3 \text{ V or } V_O = 1.4 \text{ V with } V_{DD} = 5 \text{ V}.$



[‡] Full range is -40°C to 85°C. IMPORTANT: See Parameter Measurement Information.

electrical characteristics at specified free-air temperature†

							TLV2	352M			
	PARAMETER	TEST COM	IDITIONS	T _A ‡	V	_{DD} = 3 V	1	V	_{DD} = 5 V	'	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
V10	Input offset voltage	Via – Vianmin	See Note 4	25°C		1	5		1	5	mV
VIO	input onset voltage	V _{IC} = V _{ICR} min,	See Note 4	Full range			10			10	IIIV
lio.	Input offset current			25°C		1			1		pА
lio	input onset current			125°C			10			10	nA
l.s	Input bias current			25°C		5			5		pА
IB	input bias current			125°C			20			20	nA
	Common-mode input			25°C	0 to 2			0 to 4			
VICR	voltage range			Full range	0 to 1.75			0 to 3.75			V
1	High-level output	V 4 V		25°C		0.1			0.1		nA
ЮН	current	V _{ID} = 1 V		Full range			1			1	μА
Vai	Low-level output	V _{ID} = −1 V,	I _{OL} = 2 mA	25°C		115	300		150	400	mV
VOL	voltage	$V_{\text{ID}} = -1 \text{ V},$	IOC = 2 IIIA	Full range			600			700	IIIV
lOL	Low-level output current	V _{ID} = −1 V,	V _{OL} = 1.5 V	25°C	6	16		6	16		mA
la a	Cupply ourrent	V:= -1 V	No load	25°C		120	250		140	300	
IDD	Supply current	$V_{ID} = 1 V$,	INU IUAU	Full range			350			400	μΑ

[†] All characteristics are measured with zero common-mode input voltages unless otherwise noted.

switching characteristics, V_{DD} = 3 V, T_A = 25°C

PARAMETER	т.	EST COND	SHOUTE	TL	ı	UNIT	
PARAMETER	RAMETER TEST CONDITIONS						UNIT
Response time	$R_L = 5.1 \text{ k}\Omega$, $C_L = 100 \text{ pF}$, Se			1400	ns		

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses $V_O = 1 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or $V_O = 1.4 \text{ V}$ with $V_{DD} = 5 \text{ V}$.

switching characteristics, $V_{DD} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER		TL	UNIT					
PARAMETER			TEST CONE	OTTONS	MIN	TYP	MAX	UNIT
Response time	B 51kO (C: 100 pF8	Saa Nata E	100-mV input step with 5-mV overdrive			1300	20
Response time	$R_L = 5.1 \text{ k}\Omega$, (CL = 100 prs,	See Note 5	TTL-level input step			900	ns

[§] C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses $V_O = 1 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or $V_O = 1.4 \text{ V}$ with $V_{DD} = 5 \text{ V}$.



[‡] Full range is -55°C to 125°C. IMPORTANT: See Parameter Measurement Information.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with V_{DD} = 5 V, 2 V with V_{DD} = 3 V, or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

TLV2352, TLV2352Y LinCMOS™ DUAL LOW-VOLTAGE DIFFERENTIAL COMPARATORS

SLCS011B - MAY 1992 - REVISED MARCH 1999

electrical characteristics at specified free-air temperature, $T_A = 25^{\circ}C^{\dagger}$

						TLV2	352Y			
	PARAMETER	TEST CON	V	DD = 3 \	/	V _{DD} = 5 V			UNIT	
				MIN	TYP	MAX	MIN	TYP	MAX	
V _{IO}	Input offset voltage	$V_{IC} = V_{ICR}min,$	See Note 4		1	5		1	5	mV
I _{IO}	Input offset current				1			1		pA
I_{IB}	Input bias current				5			5		pA
VICR	Common-mode input voltage range			0 to 2			0 to 4			V
loh	High-level output current	V _{ID} = 1 V			0.1			0.1		nA
VOL	Low-level output voltage	$V_{ID} = -1 V$,	$I_{OL} = 2 \text{ mA}$		115	300		150	400	mV
loL	Low-level output current	$V_{ID} = -1 V$,	V _{OL} = 1.5 V	6	16		6	16		mA
I_{DD}	Supply current	V _{ID} = 1 V	No load		120	250		140	300	μΑ

[†] All characteristics are measured with zero common-mode input voltages unless otherwise noted.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V with V_{DD} = 5 V, 2 V with V_{DD} = 3 V, or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

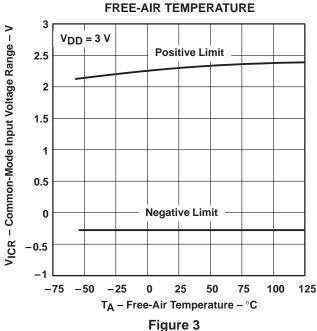


SUPPLY CURRENT

TYPICAL CHARACTERISTICS

LOW-LEVEL OUTPUT VOLTAGE **LOW-LEVEL OUTPUT CURRENT** 1100 $V_{DD} = 3 V$ 990 T_A = 25°C VOL - Low-Level Output Voltage - mV 880 770 660 550 440 330 220 110 0 0 8 10 12 14 16 I_{OL} – Low-Level Output Current – mA Figure 1

COMMON-MODE INPUT VOLTAGE RANGE vs

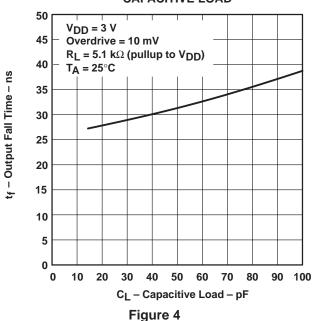


FREE-AIR TEMPERATURE 190 No Load 180 170 I_{DD} - Supply Current - μA 160 $V_{DD} = 5 V$ 150 140 $V_{DD} = 3 V$ 130 120 110 100 90 _75 - 50 - 25 25 50 75 100 125

Figure 2

OUTPUT FALL TIME vs CAPACITIVE LOAD

T_A - Free-Air Temperature - °C



TYPICAL CHARACTERISTICS

HIGH-TO-LOW-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS OVERDRIVE VOLTAGES

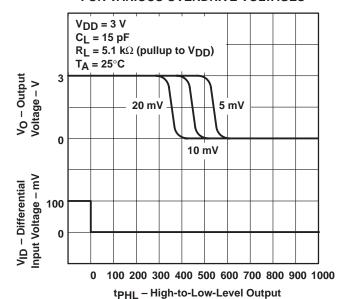


Figure 5

LOW-TO-HIGH-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS OVERDRIVE VOLTAGES

Propagation Delay Time - ns

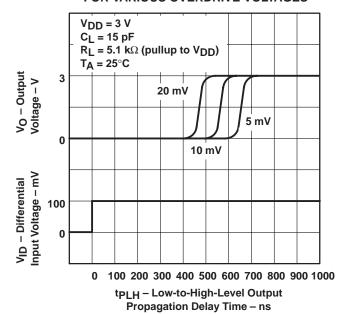


Figure 7

HIGH-TO-LOW-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS CAPACITIVE LOADS

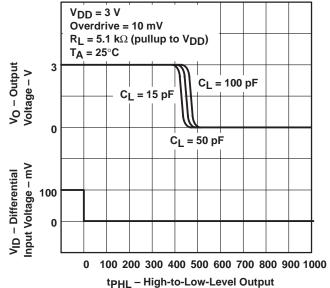
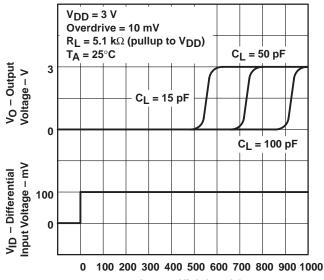


Figure 6

LOW-TO-HIGH-LEVEL OUTPUT PROPAGATION DELAY FOR VARIOUS CAPACITIVE LOADS

Propagation Delay Time - ns



tpLH - Low-to-High-Level Output Propagation Delay Time - ns

Figure 8



PARAMETER MEASUREMENT INFORMATION

The digital output stage of the TLV2352 can be damaged if it is held in the linear region of the transfer curve. Conventional operational amplifier/comparator testing incorporates the use of a servo loop that is designed to force the device output to a level within this linear region. Since the servo-loop method of testing cannot be used, the following alternatives for measuring parameters such as input offset voltage, common-mode rejection, etc., are offered.

To verify that the input offset voltage falls within the limits specified, the limit value is applied to the input as shown in Figure 9(a). With the noninverting input positive with respect to the inverting input, the output should be high. With the input polarity reversed, the output should be low.

A similar test can be made to verify the input offset voltage at the common-mode extremes. The supply voltages can be slewed as shown in Figure 9(b) for the V_{ICR} test, rather than changing the input voltages to provide greater accuracy.

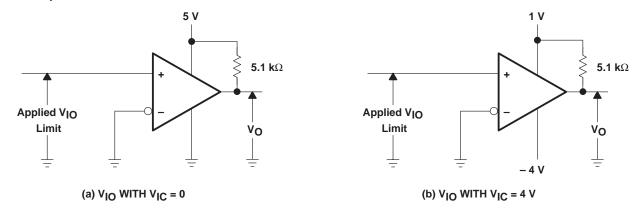


Figure 9. Method for Verifying That Input Offset Voltage Is Within Specified Limits

A close approximation of the input offset voltage can be obtained by using a binary search method to vary the differential input voltage while monitoring the output state. When the applied input voltage differential is equal but opposite in polarity to the input offset voltage, the output changes states.

PARAMETER MEASUREMENT INFORMATION

Figure 10 illustrates a practical circuit for direct dc measurement of input offset voltage that does not bias the comparator in the linear region. The circuit consists of a switching-mode servo loop in which U1a generates a triangular waveform of approximately 20-mV amplitude. U1b acts as a buffer with C2 and R4 removing any residual dc offset. The signal is then applied to the inverting input of the comparator under test while the noninverting input is driven by the output of the integrator formed by U1c through the voltage divider formed by R9 and R10. The loop reaches a stable operating point when the output of the comparator under test has a duty cycle of exactly 50%, which can only occur when the incoming triangle wave is sliced symmetrically or when the voltage at the noninverting input exactly equals the input offset voltage.

Voltage dividers R9 and R10 provide a step up of the input offset voltage by a factor of 100 to make measurement easier. The values of R5, R8, R9, and R10 can significantly influence the accuracy of the reading; therefore, it is suggested that their tolerance level be 1% or lower.

Measuring the extremely low values of input current requires isolation from all other sources of leakage current and compensation for the leakage of the test socket and board. With a good picoammeter, the socket and board leakage can be measured with no device in the socket. Subsequently, this open-socket leakage value can be subtracted from the measurement obtained with a device in the socket to obtain the actual input current of the device.

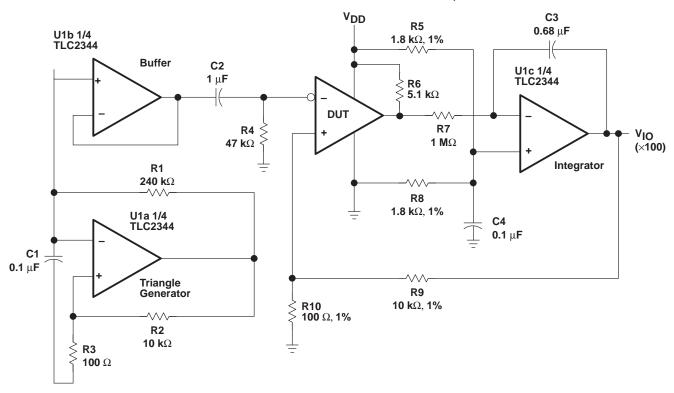
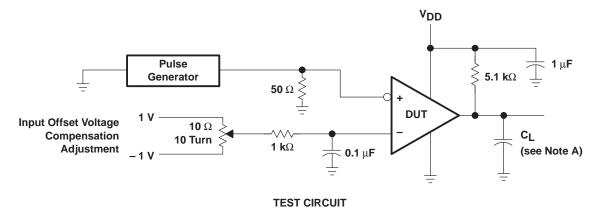


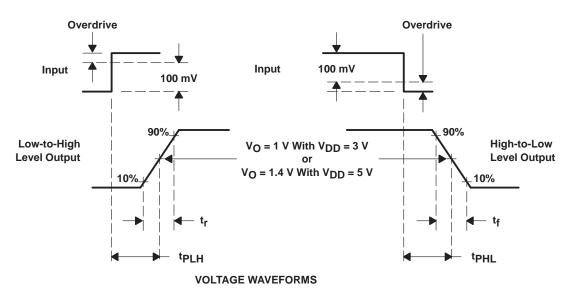
Figure 10. Circuit for Input Offset Voltage Measurement



PARAMETER MEASUREMENT INFORMATION

Propagation delay time is defined as the interval between the application of an input step function and the instant when the output crosses $V_O = 1.4 \text{ V}$ with $V_{DD} = 3 \text{ V}$ or when the output crosses $V_O = 1.4 \text{ V}$ with $V_{DD} = 5 \text{ V}$. Propagation delay time, low-to-high-level output, is measured from the leading edge of the input pulse while propagation delay time, high-to-low-level output, is measured from the trailing edge of the input pulse. Propagation-delay-time measurement at low input signal levels can be greatly affected by the input offset voltage. The offset voltage should be balanced by the adjustment at the inverting input (as shown in Figure 11) so that the circuit is just at the transition point. Then a low signal, for example 105-mV or 5-mV overdrive, causes the output to change states.





NOTE A: C_L includes probe and jig capacitance.

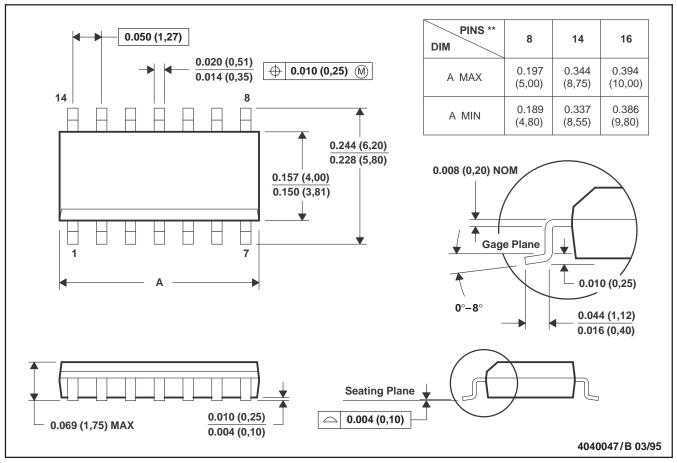
Figure 11. Propagation Delay, Rise, and Fall Times Test Circuit and Voltage Waveforms

MECHANICAL INFORMATION

D (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



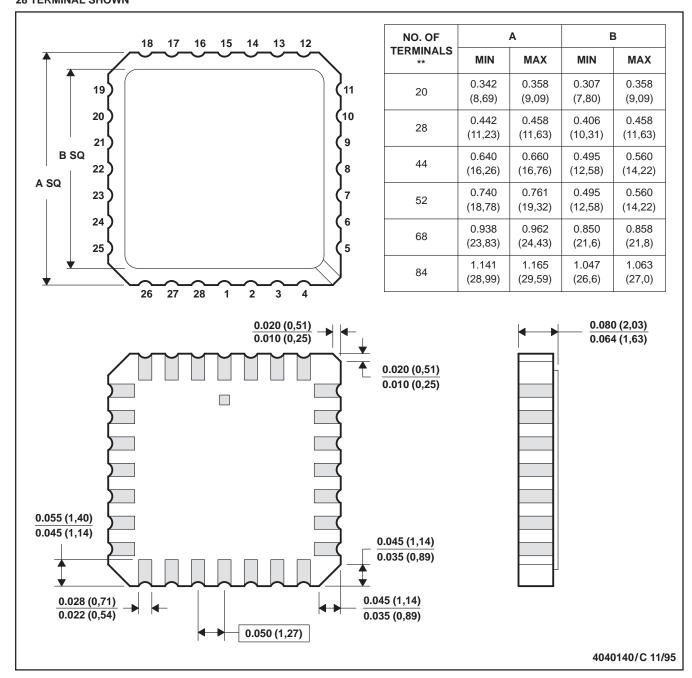
- NOTES: A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
 - D. Four center pins are connected to die mount pad.
 - E. Falls within JEDEC MS-012

MECHANICAL INFORMATION

FK (S-CQCC-N**)

28 TERMINAL SHOWN

LEADLESS CERAMIC CHIP CARRIER



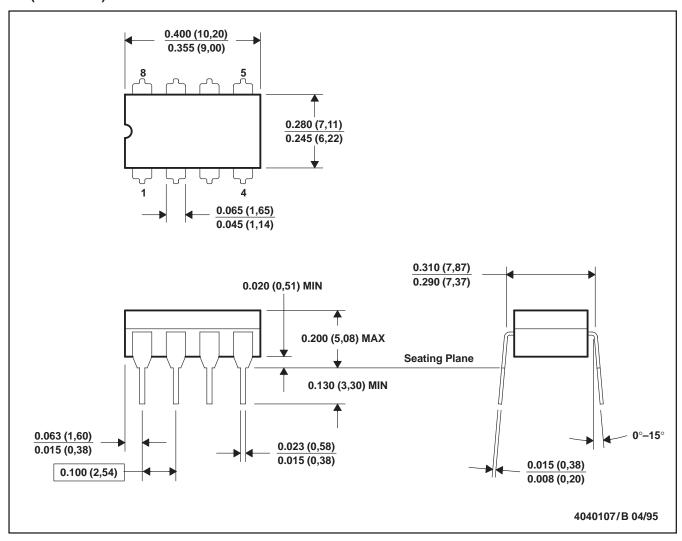
- NOTES: A. All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - C. This package can be hermetically sealed with a metal lid.
 - D. The terminals are gold plated.
 - E. Falls within JEDEC MS-004



MECHANICAL INFORMATION

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

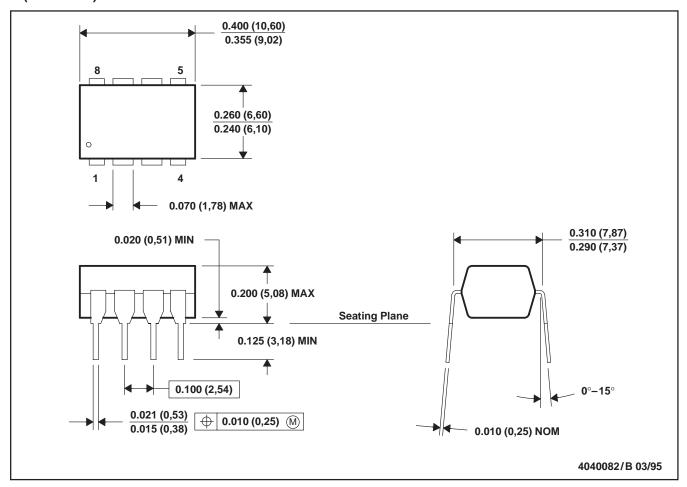
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only
- E. Falls within MIL-STD-1835 GDIP1-T8



MECHANICAL INFORMATION

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

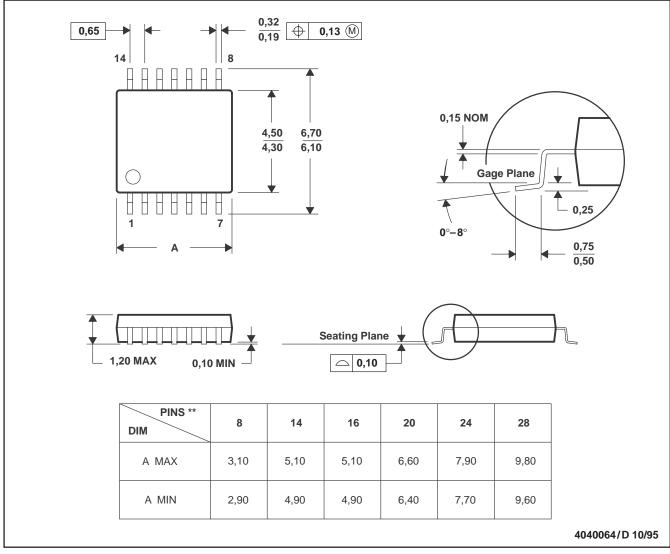
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001

MECHANICAL INFORMATION

PW (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

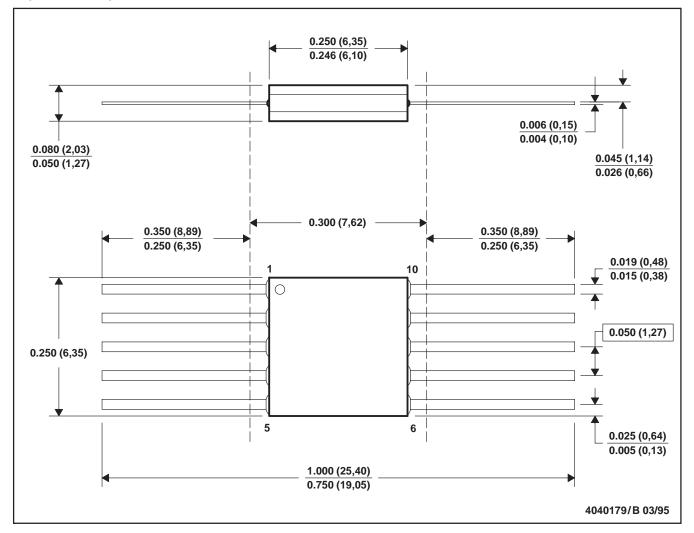
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

MECHANICAL INFORMATION

U (S-GDFP-F10)

CERAMIC DUAL FLATPACK



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F10 and JEDEC MO-092AA

www.ti.com 13-Aug-2021

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-9688101QPA	ACTIVE	CDIP	JG	8	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	9688101QPA TLV2352M	Samples
TLV2352ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	23521	Samples
TLV2352IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	23521	Samples
TLV2352IP	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLV2352IP	Samples
TLV2352IPW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY2352	Samples
TLV2352IPWG4	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY2352	Samples
TLV2352IPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY2352	Samples
TLV2352MJG	ACTIVE	CDIP	JG	8	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	TLV2352MJG	Samples
TLV2352MJGB	ACTIVE	CDIP	JG	8	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	9688101QPA TLV2352M	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

PACKAGE OPTION ADDENDUM

www.ti.com 13-Aug-2021

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLV2352, TLV2352M:

Catalog : TLV2352

Military: TLV2352M

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

• Military - QML certified for Military and Defense Applications

www.ti.com 23-Jul-2021

TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
ı	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2352IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2352IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 23-Jul-2021



*All dimensions are nominal

Device	Package Type	Package Type Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)	
TLV2352IDR	SOIC	D	8	2500	340.5	336.1	25.0	
TLV2352IPWR	TSSOP	PW	8	2000	853.0	449.0	35.0	

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale (https://www.ti.com/legal/termsofsale.html) or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2021, Texas Instruments Incorporated